

PATENT NUMBER

O.I.P. 5 380 FA SCANNED AC3 G.A.	PATENT DATE
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APPLICATION NO. 09/902483	CONT/PRIOR D	CLASS 438	SUBCLASS 602	ART UNIT 2813	EXAMINER KIEUN
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Self-aligned silicide (salicide) process for low resistivity contacts to thin film silicon-on-insulator and bulk MOSFETS and for shallow junctions

PTO-2040
12/89

ORIGINAL			CROSS REFERENCE(S)							
CLASS		SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)						
INTERNATIONAL CLASSIFICATION										

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<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
<input checked="" type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	_____ (Assistant Examiner) _____ (Date)			NOTICE OF ALLOWANCE MAILED	
<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S. Patent. No. _____	_____ (Primary Examiner) _____ (Date)			ISSUE FEE	
				Amount Due	Date Paid
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